



### General Description

- 100% UIS Tested
- Advanced Trench Technology
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

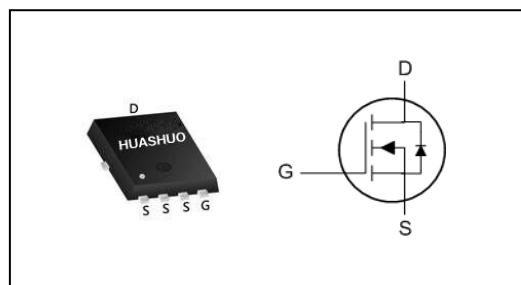
### Product Summary

V <sub>DS</sub>	30	V
R <sub>DS(ON),typ</sub>	1.3	mΩ
I <sub>D</sub>	100	A

### Applications

- Power Management in Desktop Computer
- DC/DC Converters

### PRPAK5X6 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>c</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1,6</sub>	100	A
I <sub>D</sub> @T <sub>c</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1,6</sub>	97	A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1</sub>	31	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1</sub>	25	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	350	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	151	mJ
I <sub>AS</sub>	Avalanche Current	55	A
P <sub>D</sub> @T <sub>c</sub> =25°C	Total Power Dissipation <sup>4</sup>	63	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	50	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	2	°C/W



**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}$ , $\text{I}_D=250\mu\text{A}$	30	---	---	V
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance <sup>2</sup>	$\text{V}_{\text{GS}}=10\text{V}$ , $\text{I}_D=20\text{A}$	---	1.3	1.6	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=4.5\text{V}$ , $\text{I}_D=20\text{A}$	---	1.9	2.5	
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}$ , $\text{I}_D=250\mu\text{A}$	1.2	1.6	2.2	V
$\text{I}_{\text{DSS}}$	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=24\text{V}$ , $\text{V}_{\text{GS}}=0\text{V}$ , $T_J=25^{\circ}\text{C}$	---	---	1	$\text{uA}$
		$\text{V}_{\text{DS}}=24\text{V}$ , $\text{V}_{\text{GS}}=0\text{V}$ , $T_J=55^{\circ}\text{C}$	---	---	5	
$\text{I}_{\text{GSS}}$	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 20\text{V}$ , $\text{V}_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	$\text{nA}$
$\text{g}_{\text{fs}}$	Forward Transconductance	$\text{V}_{\text{DS}}=5\text{V}$ , $\text{I}_D=20\text{A}$	---	35	---	S
$\text{R}_{\text{g}}$	Gate Resistance	$\text{V}_{\text{DS}}=0\text{V}$ , $\text{V}_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	1.0	---	$\Omega$
$\text{Q}_{\text{g}}$	Total Gate Charge (4.5V)	$\text{V}_{\text{DS}}=15\text{V}$ , $\text{V}_{\text{GS}}=10\text{V}$ , $\text{I}_D=20\text{A}$	---	45	---	$\text{nC}$
$\text{Q}_{\text{gs}}$	Gate-Source Charge		---	9.8	---	
$\text{Q}_{\text{gd}}$	Gate-Drain Charge		---	6.5	---	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time	$\text{V}_{\text{DD}}=15\text{V}$ , $\text{V}_{\text{GS}}=10\text{V}$ , $\text{R}_{\text{g}}=3.3\Omega$ , $\text{I}_D=20\text{A}$	---	10.3	---	$\text{ns}$
$\text{T}_{\text{r}}$	Rise Time		---	6.2	---	
$\text{T}_{\text{d(off)}}$	Turn-Off Delay Time		---	56	---	
$\text{T}_{\text{f}}$	Fall Time		---	8.4	---	
$\text{C}_{\text{iss}}$	Input Capacitance	$\text{V}_{\text{DS}}=15\text{V}$ , $\text{V}_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	3432	---	$\text{pF}$
$\text{C}_{\text{oss}}$	Output Capacitance		---	1916	---	
$\text{C}_{\text{rss}}$	Reverse Transfer Capacitance		---	196	---	

**Diode Characteristics**

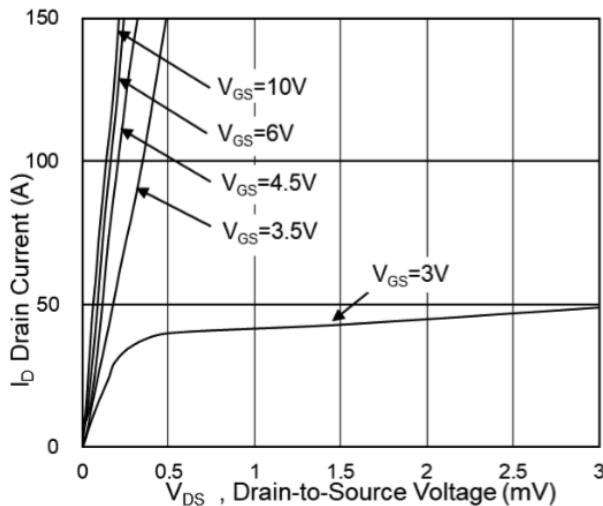
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{I}_{\text{s}}$	Continuous Source Current <sup>1,6</sup>	$\text{V}_{\text{G}}=\text{V}_{\text{D}}=0\text{V}$ , Force Current	---	---	100	A
$\text{V}_{\text{SD}}$	Diode Forward Voltage <sup>2</sup>	$\text{V}_{\text{GS}}=0\text{V}$ , $\text{I}_{\text{s}}=1\text{A}$ , $T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

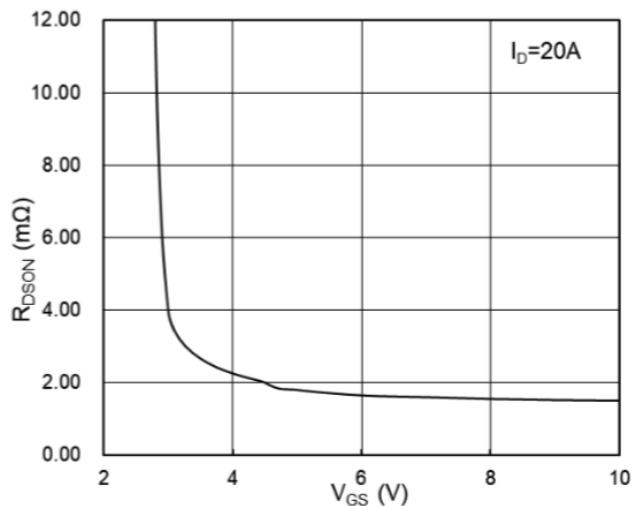
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $\text{V}_{\text{DD}}=25\text{V}$ , $\text{V}_{\text{GS}}=10\text{V}$ , $\text{L}=0.1\text{mH}$ , $\text{I}_{\text{AS}}=55\text{A}$
- 4.The power dissipation is limited by  $150^{\circ}\text{C}$  junction temperature
- 5.The data is theoretically the same as  $\text{I}_D$  and  $\text{I}_{\text{DM}}$  , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 85A.



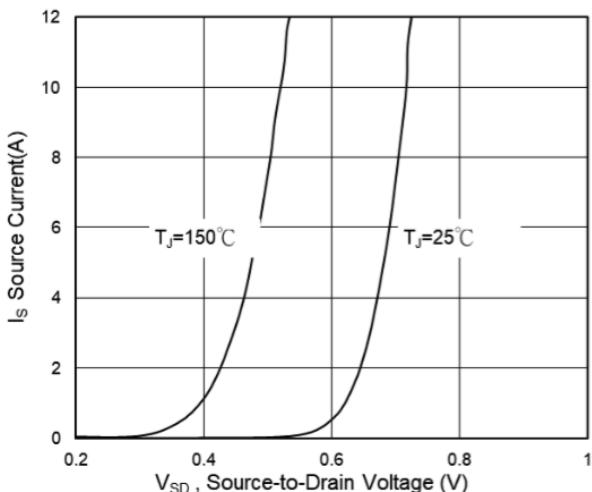
### Typical Characteristics



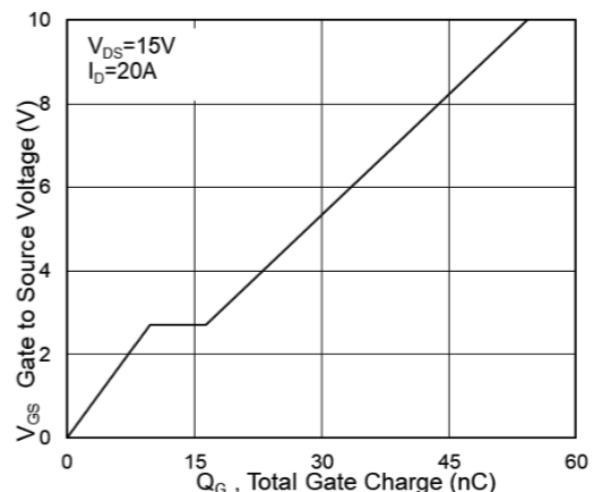
**Fig.1 Typical Output Characteristics**



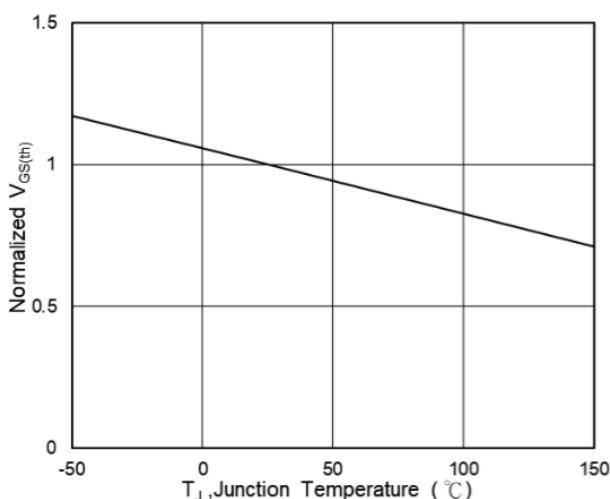
**Fig.2 On-Resistance vs G-S Voltage**



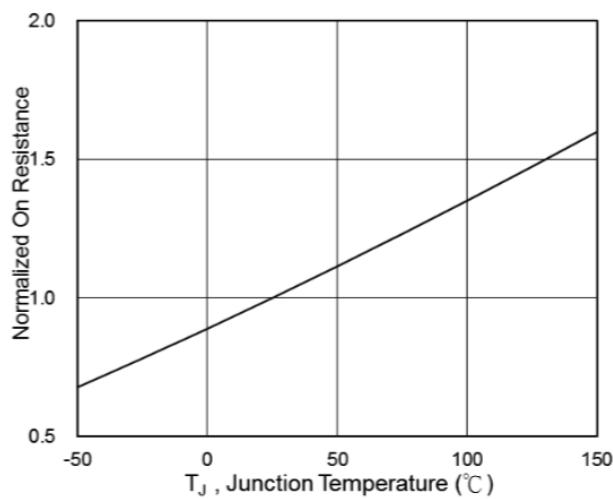
**Fig.3 Source Drain Forward Characteristics**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**



N-Ch 30V Fast Switching MOSFETs

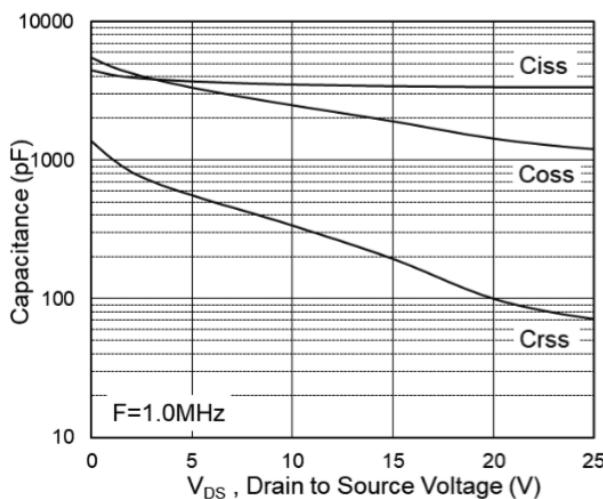


Fig.7 Capacitance

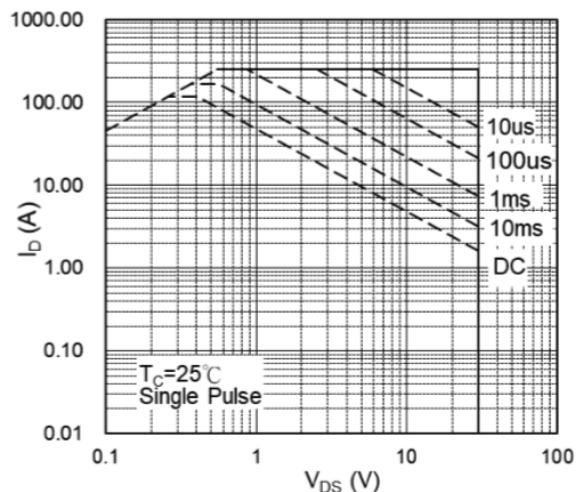


Fig.8 Safe Operating Area

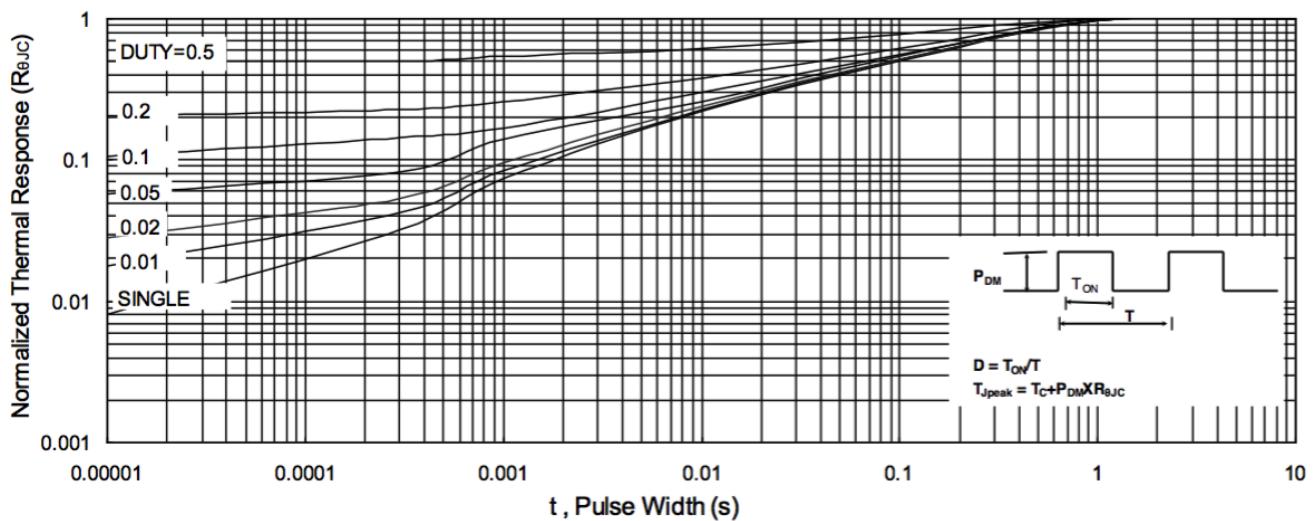


Fig.9 Normalized Maximum Transient Thermal Impedance

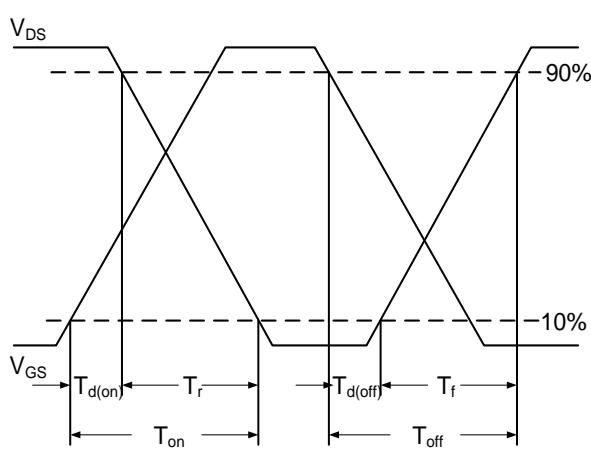


Fig.10 Switching Time Waveform

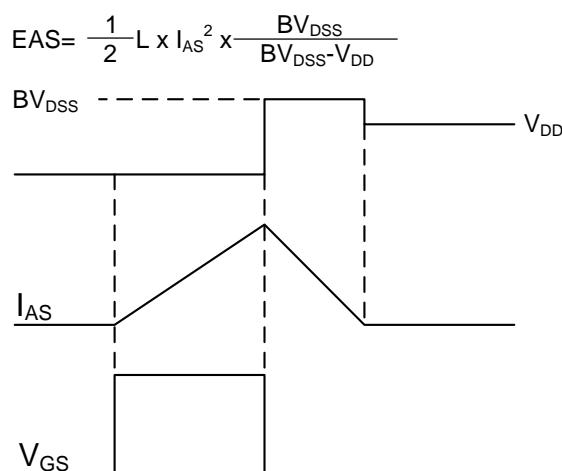
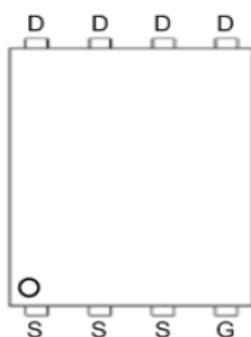
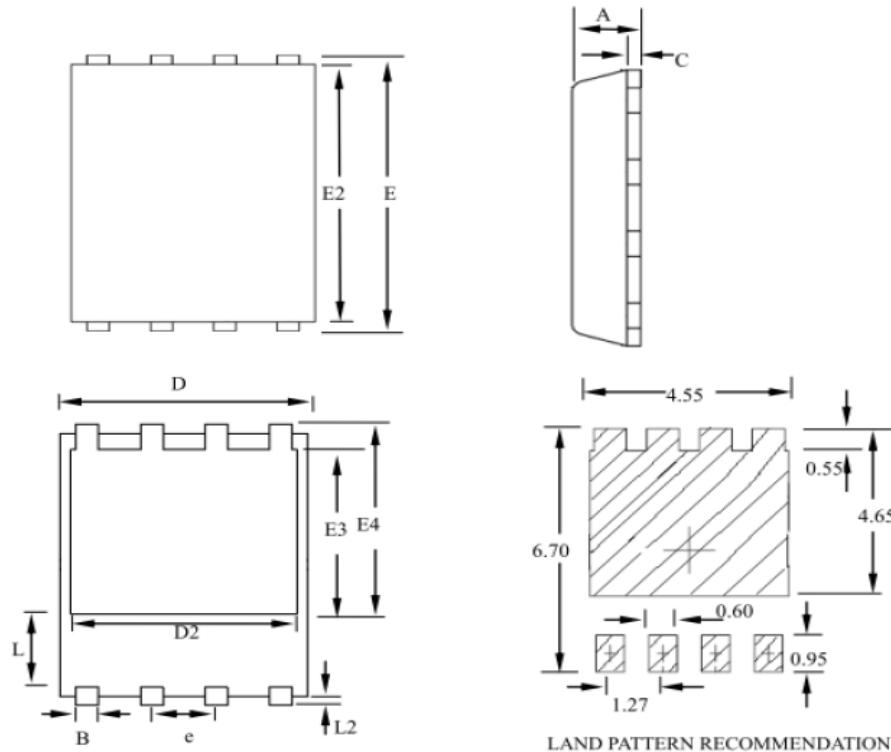


Fig.11 Unclamped Inductive Switching



## Ordering Information

Part Number	Package code	Packaging
HSBA3048	PRPAK5*6	3000/Tape&Reel



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--